



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
NPN SILICON Transistor**

VOLTAGE 60 Volts CURRENT 6 Ampere

CHT3055ZGP

APPLICATION

- * Telephony and professional communication equipment.
- * Other switching applications.

FEATURE

- * Small flat package. (SC-73/SOT-223)
- * Suitable for high packing density.
- * High saturation current capability.

CONSTRUCTION

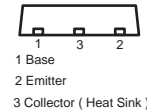
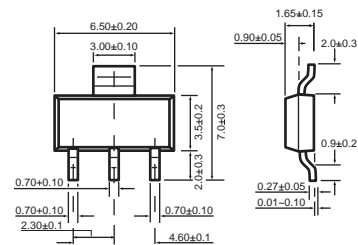
*NPN SILICON Transistor

MARKING

* ZDN



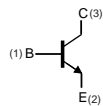
SC-73/SOT-223



Dimensions in millimeters

SC-73/SOT-223

CIRCUIT



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	—	100	V
V _{CEO}	collector-emitter voltage	open base	—	60	V
V _{EBO}	emitter-base voltage	open collector	—	7.0	V
I _C	collector current (DC)		—	6.0	A
I _B	Base Current		—	3.0	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	—	2	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		—	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT3055ZGP)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CEO}	collector cut-off current	$V_{CE}=30\text{ V}$	–	700	μA
I_{EBO}	emitter cut-off current	$V_{EB}=7.0\text{V}$	–	5.0	mA
h_{FE}	DC current gain	$I_C = 4.0\text{A}; V_{CE} = 4\text{V}$ $I_C = 6.0\text{A}; V_{CE} = 4\text{V}$	20 5.0	70 –	
V_{CEsat}	collector-emitter saturation voltage	$I_C=4.0\text{A}, I_B=400\text{mA}$	–	1.1	V
V_{BEON}	base-emitter saturation voltage	$I_C = 4.0\text{A}; V_{CE} = 4\text{V}$	–	1.5	V
f_T	transition frequency	$I_C = 500\text{mA}; V_{CE} = 10\text{ V};$ $f = 1.0\text{MHz}$	2.5	–	MHz